



2N7002

#### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
001/	5Ω @ V <sub>GS</sub> = 10V	210mA
60V	7.5Ω @ V <sub>GS</sub> = 5V	170mA

### **Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Notes 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part.
   A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
  - https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (2N7002Q)

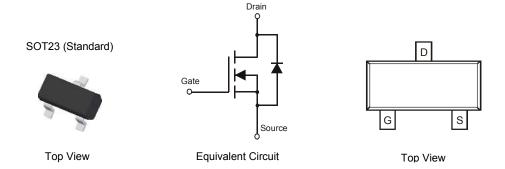
# **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(on)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Power Management Functions

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 63
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)



#### Ordering Information (Note 4)

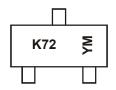
Part Number	Case	Packaging
2N7002-7-F	SOT23 (Standard)	3,000/Tape & Reel
2N7002-13-F	SOT23 (Standard)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



## **Marking Information**



K72 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: I = 2021) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2002		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	N			J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

# 

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			$V_{DSS}$	60	V
Drain-Gate Voltage R <sub>GS</sub> ≤ 1.0MΩ			$V_{DGR}$	60	V
Gate-Source Voltage		Continuous Pulsed (Note 8)	$V_{GSS}$	±20 ±40	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$ $T_A = +100^{\circ}C$	Ι <sub>D</sub>	170 120 105	mA
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$ $T_A = +100^{\circ}C$	Ι <sub>D</sub>	210 150 135	mA
Maximum Continuous Body Diode Forward Current (N	I <sub>S</sub>	0.2 0.5	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			$I_{DM}$	800	mA

## Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation	(Note 5)	C	370	mW	
Total Power Dissipation	(Note 6)	$P_{D}$	540	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 5)	C	348		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	241	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R <sub>0</sub> JC	91		
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.



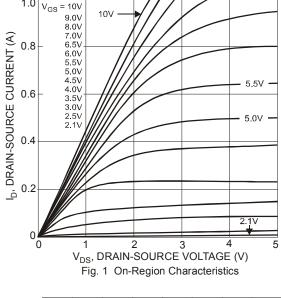
# Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

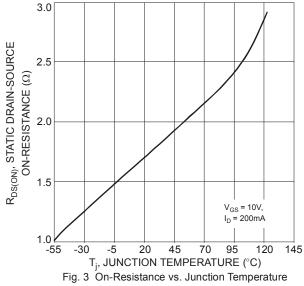
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)		•					
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	oro Gate Voltage Drain Current $\bigcirc$ T <sub>J</sub> = +25°C $\bigcirc$ T <sub>J</sub> = +125°C		_	_	1.0 500	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Body Leakage		I <sub>GSS</sub>	_	_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		$V_{GS(th)}$	1.0	_	2.5	>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance		R <sub>DS(on)</sub>	_	3.2 2.4 4.4	7.5 5.0 13.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$ $V_{GS} = 10V, I_D = 0.5A$ $V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current	•	I <sub>D(on)</sub>	0.5	1.0	_	Α	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 7.5V
Forward Transconductance		<b>g</b> FS	80	_	_	mS	V <sub>DS</sub> =10V, I <sub>D</sub> = 0.2A
Diode Forward Voltage		$V_{SD}$	_	0.78	1.5	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
DYNAMIC CHARACTERISTICS (Note 8)		•					
Input Capacitance		C <sub>iss</sub>	_	22	50	pF	
Output Capacitance		Coss	_	11	25	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Reverse Transfer Capacitance		C <sub>rss</sub>	_	2.0	5.0	pF	1.0141112
Gate Resistance		$R_g$	_	120	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)		Qg	_	223	_		
Gate-Source Charge		Qgs	_	82	_	рС	V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA
Gate-Drain Charge		$Q_{gd}$	_	178	_		
Turn-On Delay Time		t <sub>D(on)</sub>	_	2.8	_		
Turn-On Rise Time		t <sub>R</sub>	_	3.0		no	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t <sub>D(off)</sub>		7.6		ns	$R_L$ = 150 $\Omega$ , $V_{GEN}$ = 10 $V$ , $R_{GEN}$ = 25 $\Omega$
Turn-Off Fall Time		t <sub>F</sub>	_	5.6	_		- OLIV 2011

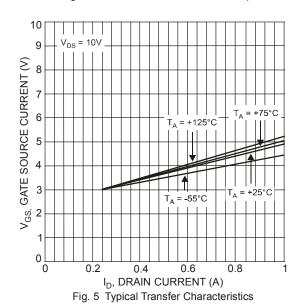
Notes:

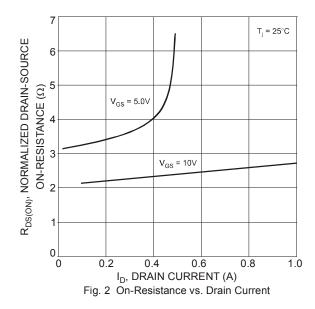
<sup>7.</sup> Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.

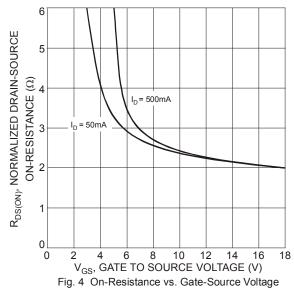












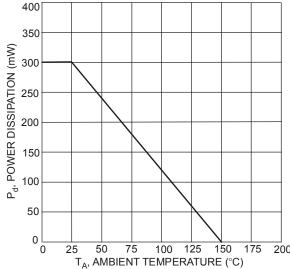


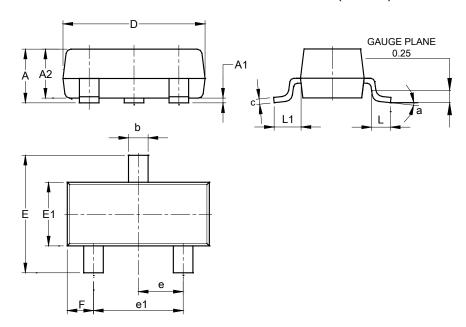
Fig. 6 Max Power Dissipation vs. Ambient Temperature



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23 (Standard)

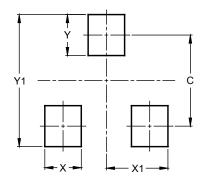


SOT23 (Standard)							
Dim	Min	Max	Тур				
Α	0.90	1.15	1.025				
A1	0.00	0.10	0.05				
A2	0.85	1.10	0.975				
b	0.30	0.51	0.40				
С	0.080	0.202	0.11				
D	2.80	3.00	2.90				
Е	2.25	2.55	2.40				
E1	1.20	1.40	1.30				
е	0.89	1.03	0.915				
e1	1.78	2.05	1.83				
F	0.40	0.60	0.535				
L1	0.45	0.61	0.55				
L	0.25	0.55	0.40				
а	0°	8°					
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23 (Standard)



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	29



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